

Abstract Submitted  
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**Charge sharing distance in silicon pixel detector.**<sup>1</sup> YUNHAO LI<sup>2</sup>, JOHN CUMALAT<sup>3</sup>, University of Colorado, Boulder, JOHN CUMALAT'S GROUP TEAM<sup>4</sup> — A simple model of charge sharing in a thin silicon pixel detector has been developed for a magnetic field free condition. This model was developed to understand the results that has been obtained from Fermilab test beam. Knowing the mean charge distribution in the planar sensor, we integrate the charge sharing that occurs from one pixel to another. The model includes thermal condition, minimum charge threshold in silicon, electron mobility, and different incidence angles. The model implements charge diffusion, and it's all based on energy loss per unit distance in silicon. The model can be used for different pixel shapes and thicknesses. We can show sharing dependence on the bias voltage and the single pixel threshold.

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